

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM6K32TU

○ Relay drive, DC/DC converter application

Unit: mm

- 4Vdrive
- Low on resistance: $R_{on} = 440\text{m}\Omega$ (max) (@ $V_{GS} = 4\text{ V}$)
 $R_{on} = 300\text{m}\Omega$ (max) (@ $V_{GS} = 10\text{ V}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

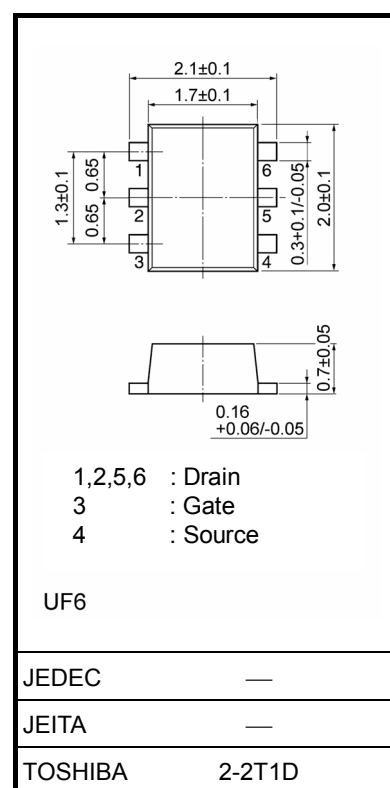
Characteristics	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	60	V
Gate-Source voltage	V_{GSS}	± 20	V
Drain current	DC I_D	2	A
	Pulse I_{DP}	6	
Drain power dissipation	P_D (Note 1)	500	mW
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	$-55\sim 150$	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on FR4 board.

(25.4 mm $\times$ 25.4 mm $\times$ 1.6 t, Cu Pad: 645 mm²)



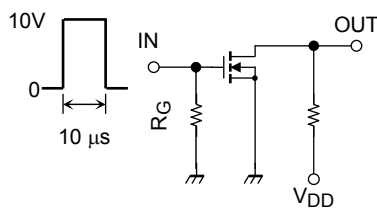
Weight: 7.0 mg (typ.)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 16\text{V}$, $V_{DS} = 0\text{V}$	—	—	± 10	μA
Drain cut-off current	I_{DSS}	$V_{DS} = 60\text{V}$, $V_{GS} = 0\text{V}$	—	—	100	μA
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{mA}$, $V_{GS} = 0\text{V}$	60	—	—	V
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{V}$, $I_D = 1\text{mA}$	0.8	—	2.0	V
Drain-Source ON resistance	$R_{DS(ON)}$	$V_{GS} = 4\text{V}$, $I_D = 1\text{A}$	—	0.33	0.44	Ω
		$V_{GS} = 10\text{V}$, $I_D = 1\text{A}$	—	0.23	0.30	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}$, $I_D = 1\text{A}$	1.0	2.0	—	S
Input capacitance	C_{iss}	$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	—	140	—	pF
Reverse transfer capacitance	C_{rss}		—	20	—	
Output capacitance	C_{oss}		—	65	—	
Switching time	Rise time t_r	$V_{DD} \doteq 30\text{V}$, $I_D = 1\text{A}$ $V_{GS} = 0\sim 10\text{V}$, $R_G = 50\Omega$	—	140	—	ns
	Turn-on time t_{on}		—	210	—	
	Fall time t_f		—	470	—	
	Turn-off time t_{off}		—	1600	—	
Total gate charge	Q_g	$V_{DD} \doteq 48\text{V}$, $V_{GS} = 10\text{V}$ $I_D = 2\text{A}$	—	5.0	—	nC
Gate-source charge	Q_{gs}		—	3.6	—	
Gate-drain charge	Q_{gd}		—	1.4	—	
Drain-Source forward voltage	V_{DSF}	$I_D = -2\text{A}$, $V_{GS} = 0\text{V}$	—	—	-1.5	V

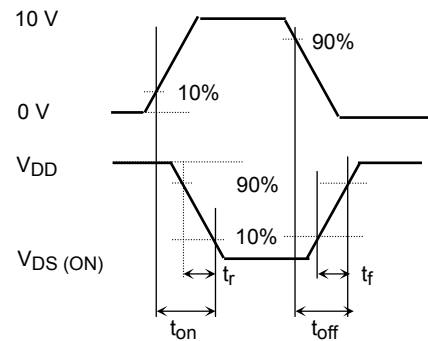
Switching Time Test Circuit

(a) Test Circuit



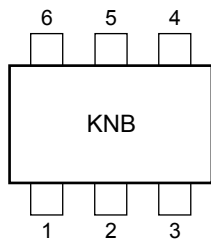
$V_{DD} \cong 30 \text{ V}$
 $R_G = 50 \Omega$
 Duty $\leq 1\%$
 V_{IN} : $t_r, t_f < 5 \text{ ns}$
 Common Source
 $T_a = 25^\circ\text{C}$

(b) V_{IN}

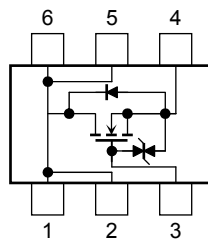


(c) V_{OUT}

Marking



Equivalent Circuit (Top View)



Precaution

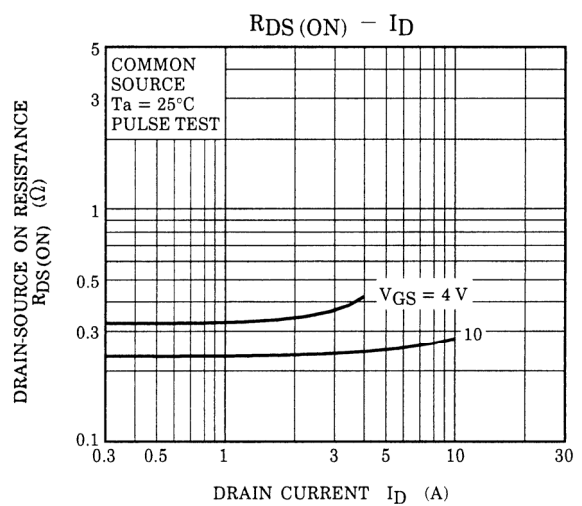
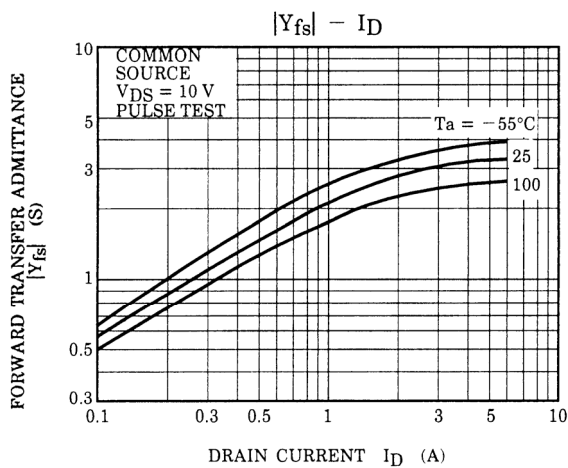
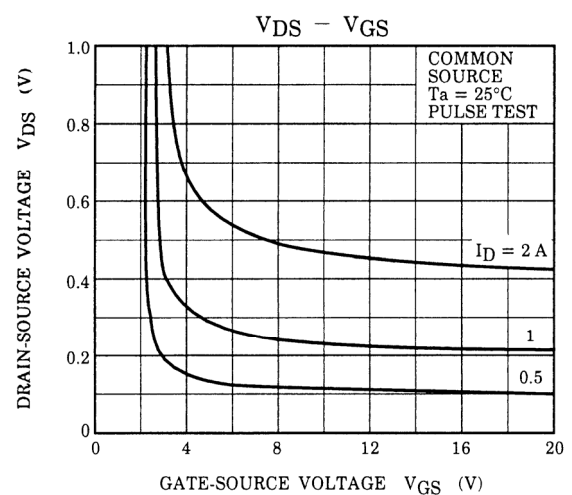
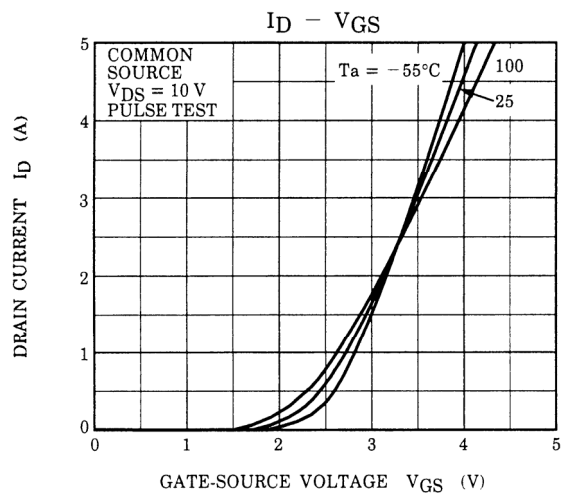
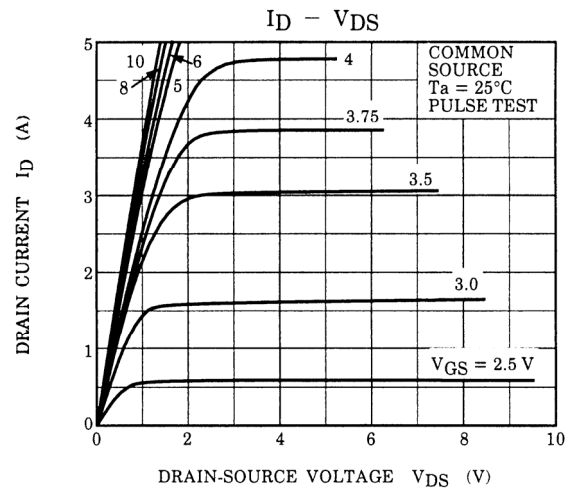
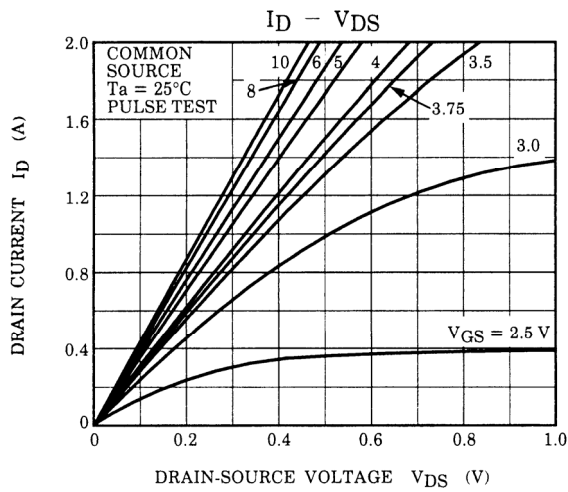
V_{th} can be expressed as the voltage between gate and source when the low operating current value is $I_D = 1 \text{ mA}$ for this product. For normal switching operation, $V_{GS(ON)}$ requires a higher voltage than V_{th} and $V_{GS(OFF)}$ requires a lower voltage than V_{th} .

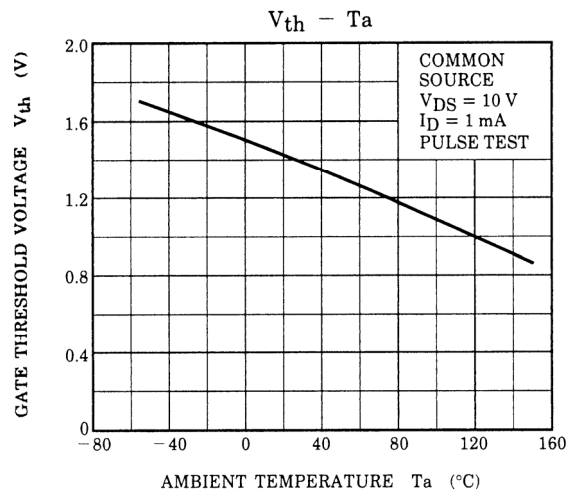
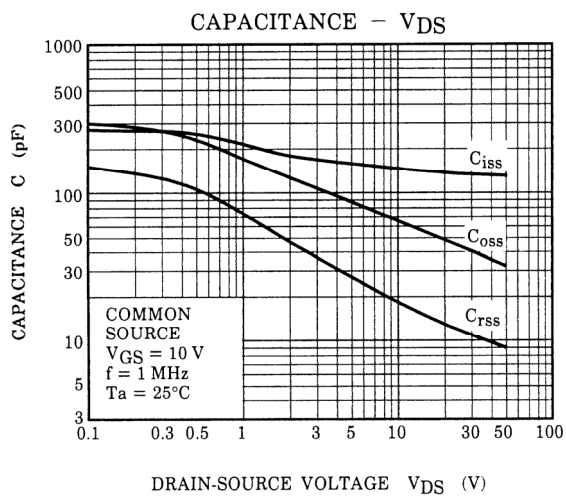
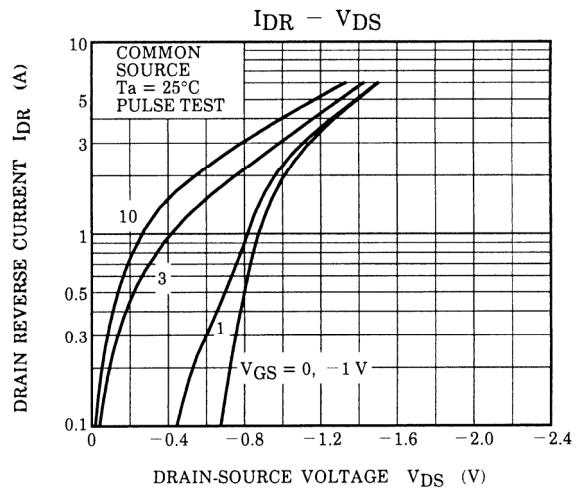
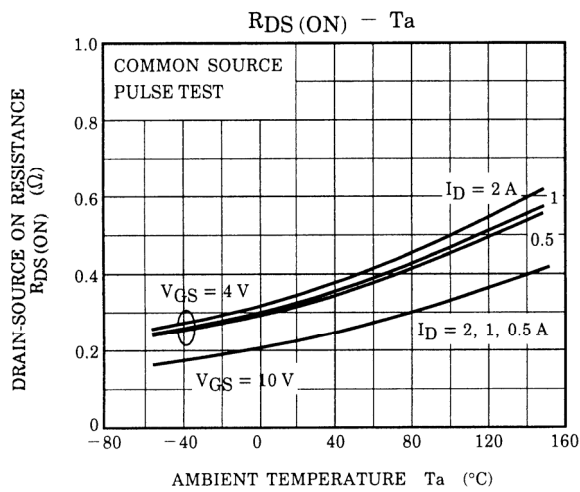
(The relationship can be established as follows: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.)

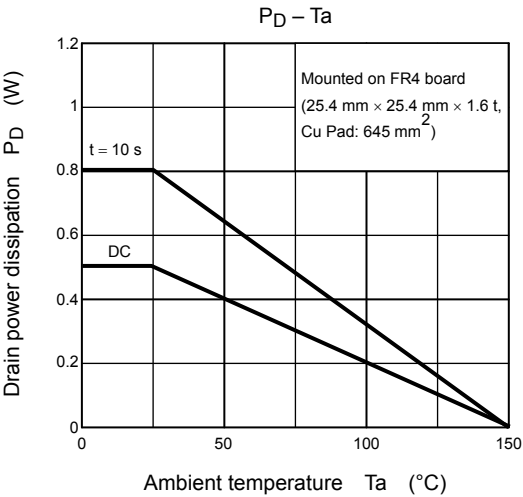
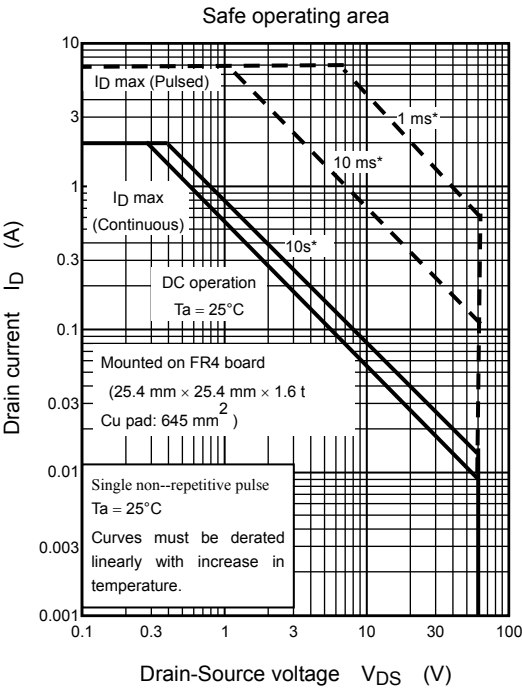
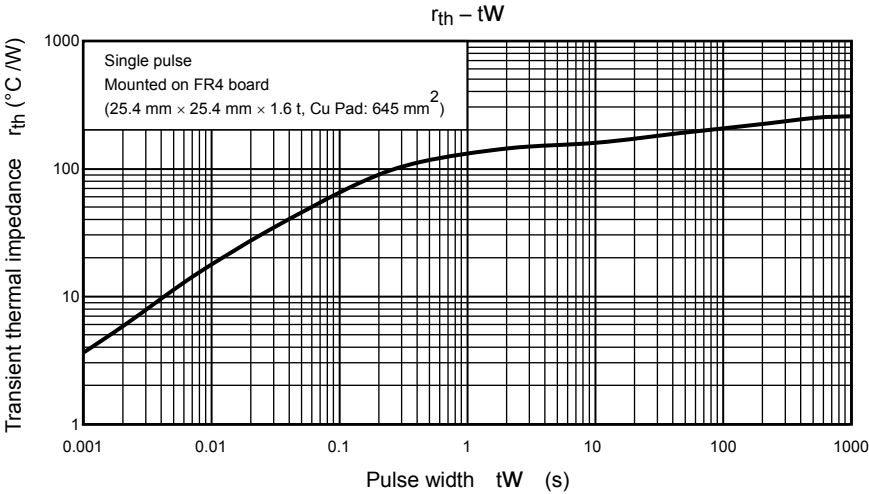
Take this into consideration when using the device.

Handling Precaution

When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.







RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
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